

#### Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-12	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-12	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Base Current	IB	-500	mA
Continuous Collector Current	Ic	-3	A
Peak Pulse Collector Current	I <sub>CM</sub>	-10	A

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)	· ,		w	
Linear Derating Factor	(Note 6)	P <sub>D</sub>	1.7 13.6	mW/°C	
Thermal Desistance, Junction to Ambient	(Note 5)	P	113	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>θJA</sub>	73		
Thermal Resistance, Junction to Leads	(Note 7)	R <sub>θJL</sub>	30.0	°C/W	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

#### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

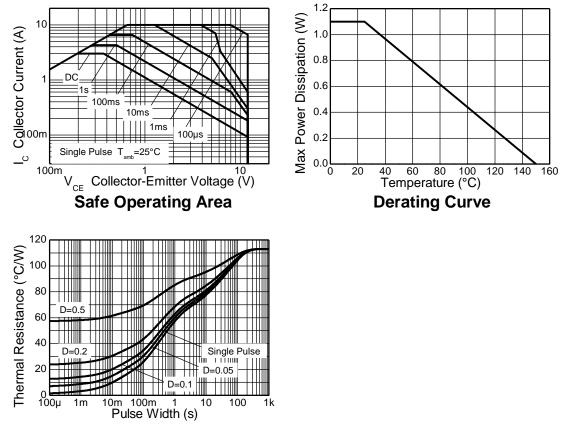
Notes: 5. For a device mounted with collector leads on 25mm x 25mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

6. Same as Note 5, except the device is measured at t  $\leq$  5 seconds.

Thermal resistance from junction to solder-point (at the end of the collector leads).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## Thermal Characteristics and Derating Information



**Transient Thermal Impedance** 





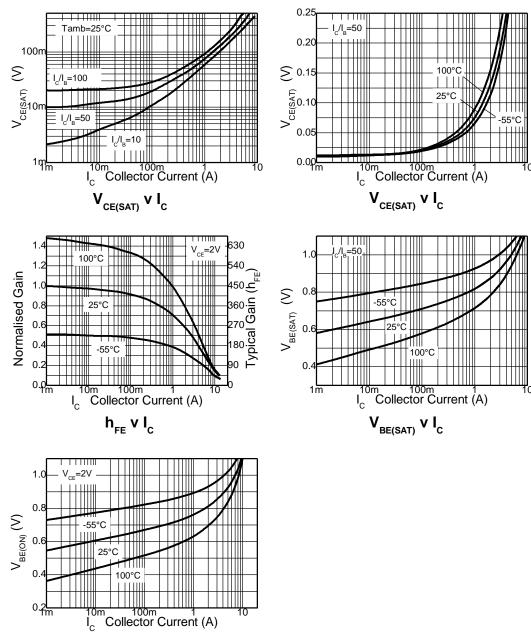
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Turn	Мах	Unit	Test Condition
OFF CHARACTERISTICS	Symbol	Min	Тур	wax	Unit	Test Condition
				[		
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-12	-35	_	V	I <sub>C</sub> = -100μΑ
Collector-Emitter Breakdown Voltage (Note 9)	BVCEO	-12	-25	_	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	-8.5	_	V	$I_E = -100\mu A$
Collector-Base Cutoff Current	I <sub>CBO</sub>		<1	-100	nA	V <sub>CB</sub> = -10V
Emitter Cutoff Current	I <sub>EBO</sub>	_	<1	-100	nA	$V_{EB} = -4V$
Collector-Emitter Cutoff Current	I <sub>CES</sub>	_	<1	-100	nA	$V_{CES} = -10V$
ON CHARACTERISTICS (Note 9)						
DC Current Gain (Note 9)		300	475			$I_{C} = -10mA, V_{CE} = -2V$
	h <sub>FE</sub>	300	450			$I_{C} = -0.1A, V_{CE} = -2V$
		180	275			$I_{C} = -2.5A, V_{CE} = -2V$
		60	100			$I_{C} = -8.0A, V_{CE} = -2V$
		45	70	_		$I_{C} = -10A, V_{CE} = -2V$
	V <sub>CE(sat)</sub>	_	-10	-17	mV	$I_{C} = -0.1A, I_{B} = -10mA$
Collector-Emitter Saturation Voltage (Note 9)		_	-100	-140		$I_{C} = -1.0A, I_{B} = -10mA$
Collector-Emilier Saturation Voltage (Note 9)		_	-100	-150		I <sub>C</sub> = -1.5A, I <sub>B</sub> = -50mA
		_	-195	-300		$I_{C} = -3.0A, I_{B} = -50mA$
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	_	-0.90	-0.95	V	$I_{C} = -3.0A, I_{B} = -50mA$
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(on)</sub>	_	-0.85	-0.90	V	$I_{C} = -3.0A, V_{CE} = -2V$
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product	f <sub>T</sub>	80	110	_	MHz	V <sub>CE</sub> = -10V, I <sub>C</sub> = -50mA, f = 100MHz
Output Capacitance	C <sub>obo</sub>	_	21	30	pF	V <sub>CB</sub> = -10V, f = 1MHz
Turn-On Time	t <sub>(on)</sub>	_	70		ns	$V_{CC} = -6V, I_C = -2A$
Turn-Off Time	t <sub>(off)</sub>	_	130	_	ns	$I_{B1} = -I_{B2} = -50 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300  $\mu s.$  Duty cycle  $\leq$  2%.



# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

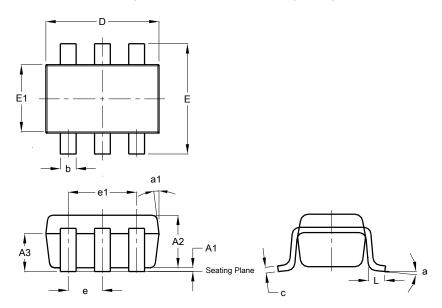


 $\mathbf{V}_{_{\mathsf{BE}(\mathsf{ON})}} ~\mathbf{v}~\mathbf{I}_{_{\mathsf{C}}}$ 



### **Package Outline Dimensions**

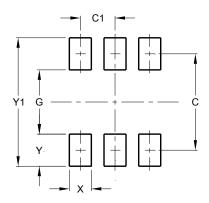
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT26				
Dim	Min	Max	Тур	
A1	0.013	0.10	0.05	
A2	1.00	1.30	1.10	
A3	0.70	0.80	0.75	
b	0.35	0.50	0.38	
c	0.10	0.20	0.15	
D	2.90	3.10	3.00	
e	-	-	0.95	
e1	-	-	1.90	
Е	2.70	3.00	2.80	
E1	1.50	1.70	1.60	
L	0.35	0.55	0.40	
а	-	-	8°	
a1	-	-	7°	
All Dimensions in mm				

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



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